
	<h2>SI1011X-T1-GE3</h2>
	<p><b>Hersteller-Teilenummer:</b> <a href="#">SI1011X-T1-GE3</a></p> <p><b>Hersteller / Marke:</b> <a href="#">Vishay / Siliconix</a></p> <p><b>Teil der Beschreibung:</b> MOSFET P-CH 12V SC-89</p> <p><b>Datenblätter:</b>  <a href="#">SI1011X-T1-GE3.pdf</a></p> <p><b>RoHs Status:</b> Bleifrei / RoHS-konform</p> <p><b>Lagerzustand:</b> New original, 51000 pcs Stock Available.</p> <p><b>Liefern von:</b> Hong Kong</p> <p><b>Versandweg:</b> DHL/Fedex/TNT/UPS/EMS</p>
<p>Image may be representation. See specs for product details.</p>	

### Spezifikationen

Teilenummer	<a href="#">SI1011X-T1-GE3</a>
Hersteller	<a href="#">Vishay / Siliconix</a>
Beschreibung	MOSFET P-CH 12V SC-89
Kategorie	<a href="#">Diskrete Halbleiterprodukte &gt; Transistoren-FETs,</a>
Teilstatus	51000 pcs Stock
Serie	TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	SC-89, SOT-490
Supplier Device-Gehäuse	SC-89-3
Verlustleistung (max)	190mW (Ta)
Typ FET	P-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	12V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	-
Rds On (Max) @ Id, Vgs	640 mOhm @ 400mA, 4.5V
VGS (th) (Max) @ Id	800mV @ 250µA
Gate Charge (Qg) (Max) @ Vgs	4nC @ 4.5V
Eingabekapazität (Ciss) (Max) @ Vds	62pF @ 6V
Antriebsspannung (Max Rds On, Min Rds On)	1.2V, 4.5V
Vgs (Max)	±5V
Verpackung	Tape & Reel (TR)





















SI1011X-T1-GE3 ist neu im Original, Suche SI1011X-T1-GE3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI1011X-T1-GE3 Vishay / Siliconix mit Garantie und Vertrauen. Anfrage SI1011X-T1-GE3: [Info@Y-IC.com](mailto:Info@Y-IC.com)

Sie können auch interessiert sein:

 <p><b>SI1011-A-GMR</b> Energy Micro (Silicon Labs) IC RF TXRX+MCU ISM&lt;1GHZ 42-WFQFN</p>	 <p><b>SI1011-C-GM2R</b> Energy Micro (Silicon Labs) IC RF TXRX+MCU ISM&lt;1GHZ 42-VFLGA</p>	 <p><b>SI1011X-T1-GE3</b> Electro-Films (EFI) / Vishay MOSFET P-CH 12V SC-89</p>	 <p><b>SI1012-A-GM</b> Energy Micro (Silicon Labs) IC RF TXRX+MCU ISM&lt;1GHZ 42-WFQFN</p>
 <p><b>SI1012-A-GMR</b> Energy Micro (Silicon Labs) IC RF TXRX+MCU ISM&lt;1GHZ 42-WFQFN</p>	 <p><b>SI1012-C-GM2</b> Energy Micro (Silicon Labs) IC RF TXRX+MCU ISM&lt;1GHZ 42-VFLGA</p>	 <p><b>SI1012-C-GM2R</b> Energy Micro (Silicon Labs) IC RF TXRX+MCU ISM&lt;1GHZ 42-VFLGA</p>	 <p><b>SI1011-C-GM2</b> Energy Micro (Silicon Labs) IC RF TXRX+MCU ISM&lt;1GHZ 42-VFLGA</p>

### heiße Teile

Mehr

 SI1000-C-GM	 SI1002-C-GMR	 SI1003-C-GM	 SI1011X-T1-GE3	 SI1012CR-T1-GE3
 SI1012CR-T1-GE3	 SI1012R-T1	 SI1012R-T1-E3	 SI1012R-T1-E3	 SI1012R-T1-GE3
 SI1012R-T1-GE3	 SI1012X-T1	 SI1012X-T1-E3	 SI1012X-T1-E3	 SI1012X-T1-GE3
 SI1012X-T1-GE3	 SI1013CX-T1-GE3	 SI1013CX-T1-GE3	 SI1013R-T1	 SI1013R-T1-E3
 SI1013R-T1-E3	 SI1013R-T1-GE3	 SI1013R-T1-GE3	 SI1013X-T1	 SI1013X-T1-E3
 SI1013X-T1-E3	 SI1013X-T1-GE3	 SI1013X-T1-GE3	 SI1016CX-T1-GE3	 SI1016CX-T1-GE3
 SI1016X-T1-E3	 SI1016X-T1-E3	 SI1016X-T1-GE3	 SI1016X-T1-GE3	 SI1016X2-T1-GE3
 SI1021R-T1	 SI1021R-T1-E3	 SI1021R-T1-E3	 SI1022R-T1	 SI1022R-T1-E3
 SI1022R-T1-E3	 SI1022R-T1-GE3	 SI1022R-T1-GE3	 SI1022R-T1-E3	 SI1023CX-T1-GE3
 SI1023CX-T1-GE3	 SI1023X-T1	 SI1023X-T1-E3	 SI1023X-T1-E3	 SI1023X-T1-GE3

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